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OKON
PATENT
1/29/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

HWANG et al.

Group Art Unit: 2814

Serial No.: 10/022,349

Examiner: D. Wille

Filed: December 20, 2001

For: A SINGLE-CHIP STRUCTURE OF SILICON GERMANIUM
PHOTODETECTOR AND HIGH-SPEED TRANSISTOR

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

This is in response to the Official Action of October 17, 2002, in connection with the above-identified application.

Please amend the above-identified application as follows.

IN THE CLAIMS:

Please replace claims 20 and 29 with the following amended claims 20 and 29.

20(Amended). A single-chip structure of silicon germanium photodetectors and high-speed transistors comprising:

a substrate;

a phototransistor, which is formed on a side of the substrate;

a high-speed bipolar transistor which is located on the opposite side of the phototransistor on substrate; and

a separated insulation-layer which separates the phototransistor and the high-speed bipolar transistor, a single-chip structure of the phototransistor and the high-speed bipolar transistor can be completely implemented on a same substrate; and

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